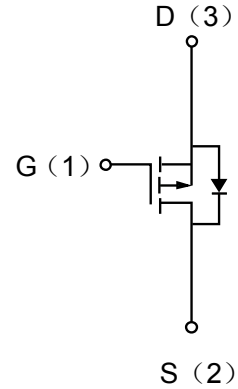


Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
-20	0.85@ V _{GS} =-4.5V	-0.8
	1.2@ V _{GS} =-2.5V	-0.5


Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = -250μA, V _{GS} = 0V	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±10V	-	-	±1	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.35		-1	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -4.5V, I _D = -0.8A	-	-	0.85	Ω
		V _{GS} = -2.5V, I _D = -0.5A	-	-	1.2	Ω
Forward Tran conductance	g _{FS}	V _{GS} = 5V, I _D = 50mA, T _A = 125°C		6.5		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = -6V, f = 200KMHz	-	200		pF
Output Capacitance	C _{DSS}		-	80		pF
Reverse Transfer Capacitance	C _{RSS}		-	150		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6V, V _{GS} = -4.5V, R _L = 6Ω, R _G = 6Ω, I _D = -1A	-		17	ns
Turn-Off Delay Time	t _{d(off)}		-		65	ns

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	V
Drain Current	Continuous	I_D	-0.8	A
	Pulsed	I_D	-3	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	250	mW
	$T_A=125^\circ\text{C}$	P_D	200	mW

Typical Characteristics

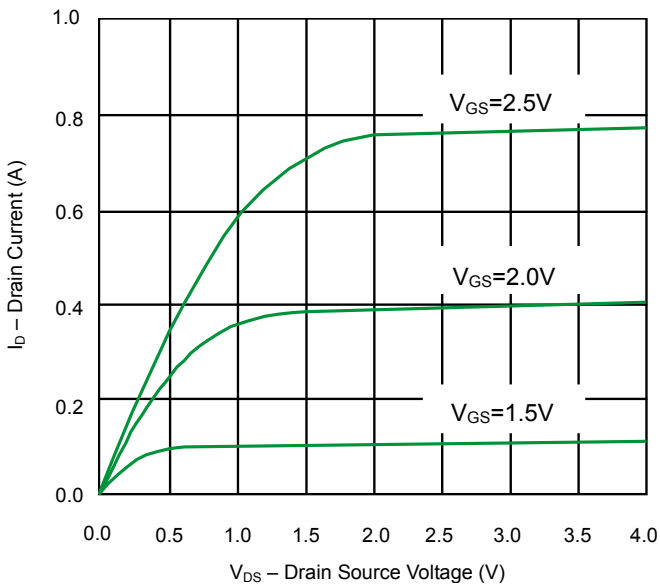


Fig 1. Output Characteristics

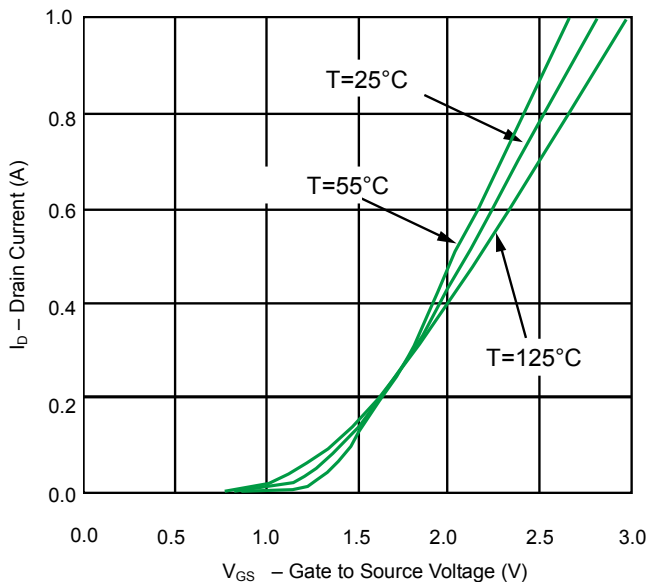


Fig 2. Transfer Characteristics

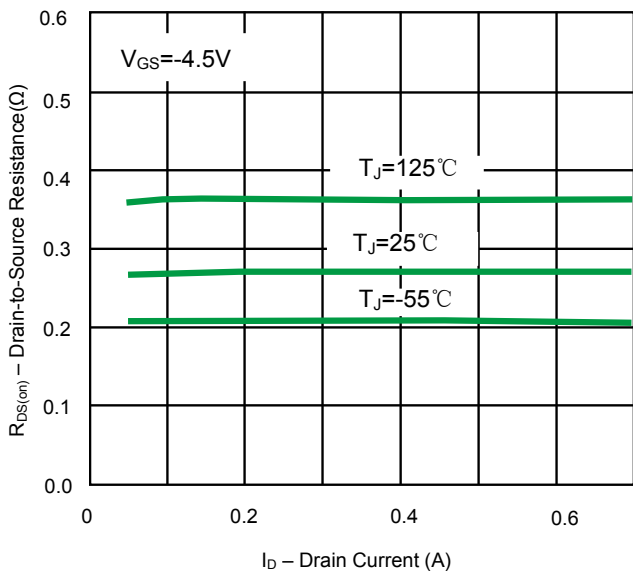


Fig 3. On-Resistance vs. Drain Current

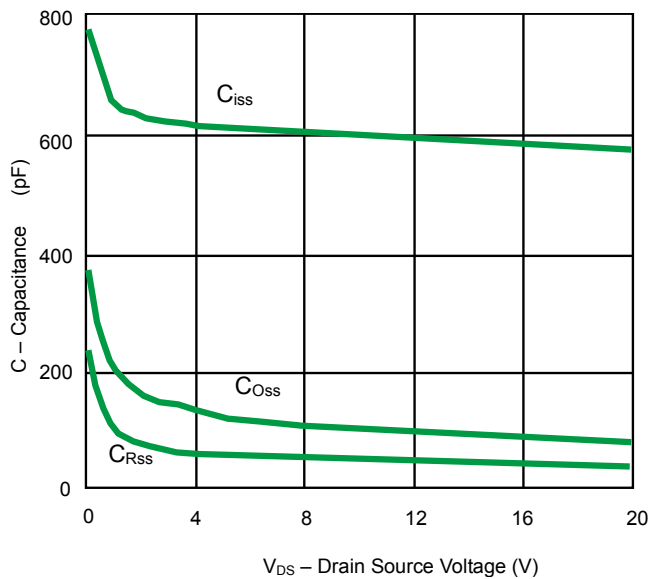
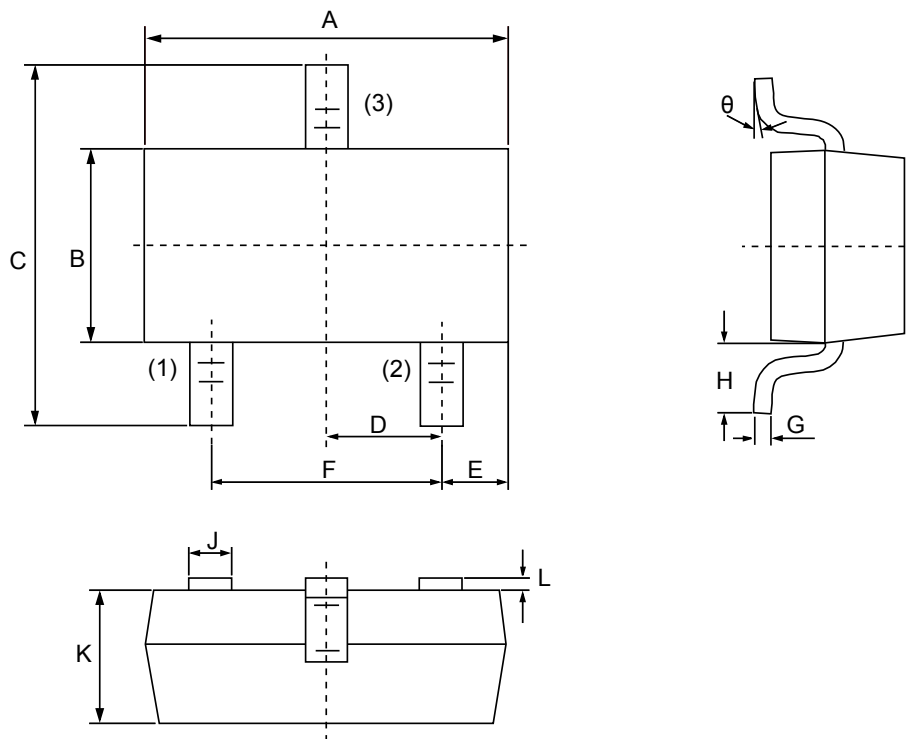



Fig 4. Capacitance

Product dimension (SOT-523)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	1.50	1.70	0.059	0.067
B	0.75	0.85	0.030	0.033
C	1.450	1.750	0.057	0.069
D	0.50BSC		0.020BSC	
E	0.30	0.33	0.012	0.015
F	0.900	1.100	0.035	0.043
G	0.100	0.200	0.004	0.008
H	0.550		0.022	
J	0.150	0.250	0.006	0.010
K	0.700	0.900	0.028	0.038
L	0.024	0.027	0.600	0.700
θ	0°	4°	0°	4°


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